

isc P-Channel MOSFET Transistor

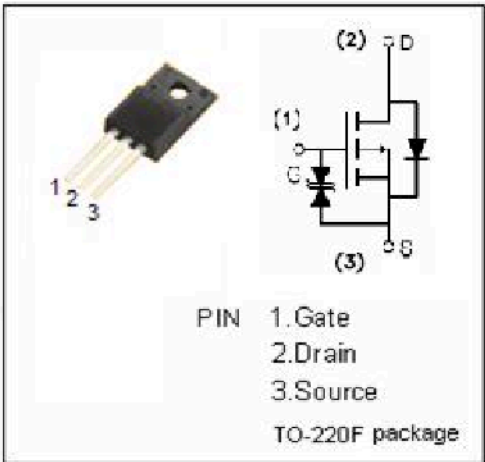
2SJ374

DESCRIPTION

- Low Drain-Source ON Resistance
- High Forward Transfer Admittance
- Low Leakage Current
- Enhancement-Mode

APPLICATIONS

- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application

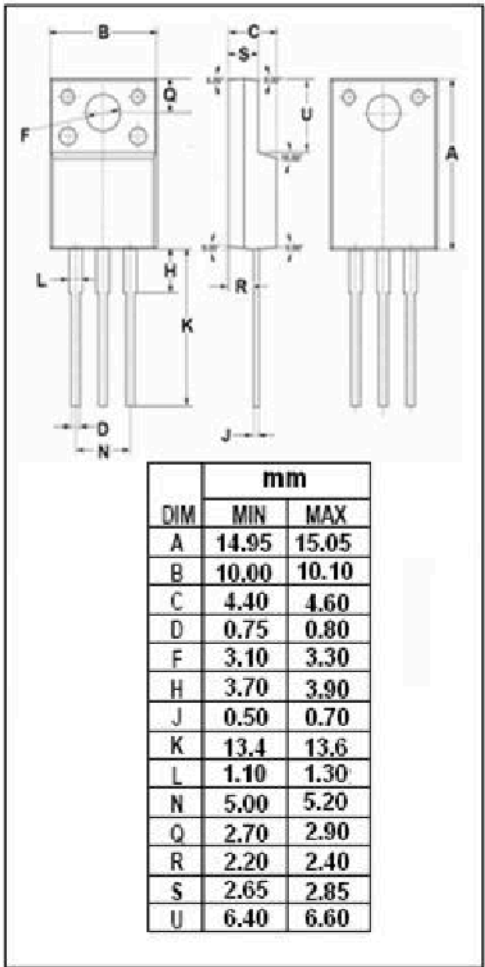


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	-60	V
V_{GS}	Gate-Source Voltage	± 15	V
I_D	Drain Current-continuous@ $TC=37^{\circ}\text{C}$	-20	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}\text{C}$	40	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	3.1	$^{\circ}\text{C/W}$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	75	$^{\circ}\text{C/W}$



isc P-Channel Mosfet Transistor**2SJ374****• ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=-1\text{mA}$	-60		V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=-1\text{mA}$	-1.0	-2	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=-10\text{V}; I_D=-7.5\text{A}$		0.07	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=-12\text{V}; V_{DS}=0$		-10	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-60\text{V}; V_{GS}=0$		-0.1	mA
V_{SD}	Diode Forward Voltage	$I_F=-20\text{A}; V_{GS}=0$		-1.5	V